

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	semiconductor and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 07:40
S2	1	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:13
S3	0	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) with (buried adj oxide) with (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) with (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:13
S4	3	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) same (buried adj oxide) same (implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")) same (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:14
S5	87	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and (implant\$6 or dop\$6) and (hydrogen or ("H.sub.2")) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:14
S6	83	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) with (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:15
S7	55	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 07:42
S8	30	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	USPAT	OR	ON	2005/06/06 15:17

S9	28	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2"))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/10 07:43
S10	19	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2"))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/06 15:18
S11	24	semiconductor and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2"))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/06/07 06:16
S12	663	(438/458).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 09:10
S13	991	(438/455).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 10:06
S14	799	(438/459).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 09:30
S15	880	(438/404).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
S16	366	(438/406).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41

S17	188	(438/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
S18	175	(438/423).CCLS.	US-PGPUB, USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 07:41
S19	40	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:10
S20	24	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	USPAT	OR	ON	2005/09/16 09:30
S23	701	(438/458).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 09:10
S24	41	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:11
S25	0	("438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S26	0	("438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12

S27	0	("257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S28	0	("257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)).clm.	US-PGPUB	OR	ON	2005/09/16 09:12
S29	0	("438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)).clm.	US-PGPUB	OR	ON	2005/09/16 09:12
S30	828	(438/459).CCLS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 09:30
S31	28	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:31
S32	14	"257"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:31
S33	10	"438"/404,406,407,423,455,459, 458.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2")))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:31

S34	15	"438"/\$.ccls. and (((silicon or ("Si")) adj on adj insulator) or ("SOI")) and (buried adj oxide) and ((implant\$6 or dop\$6) near (hydrogen or ("H.sub.2"))) and (rare adj gas)) and @ad<="20030226" and delaminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:32
S35	1047	(438/455).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 10:06
S36	637	yokokawa.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:07
S37	61	S36 and isao	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10
S38	22	S37 and SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10